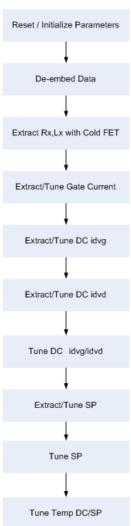
4.2 Hand-Scripts of Angelov Model Parameter Extractions

4.3 Notes on the IC-CAP Help Doc

4.3.1 Parameter Extraction Flow Example

0. Example Parameter Extraction Flow

Based on the parameter extraction flow, following is an example parameter extraction flow to see that DC matches with S-parameter of vgm2.



The following is an orderly description about example extraction flow using the sample data loaded in the Angelov-GaN Toolkit.

1. Initialize

Reset Parameter to Defaults

Reset the values of Model Parameters to the default before you begin the Extraction.

Initialize Parameter and Boundaries for Extraction

Initialize the values of Model Parameters, Opt Min and Opt Max before you begin the Extraction.

Update All Measures Data for Extraction

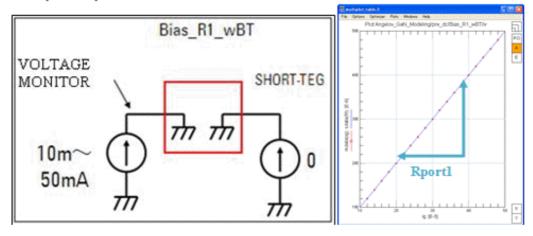
Perform PEL calculation and De-embed with respect to all the data, and update before you begin the extraction.

2. DC Port Resistance

PreDC Port1

Calculate Rport1, the DC Path Resistance of Port1 side from the Slope using E:Rport1

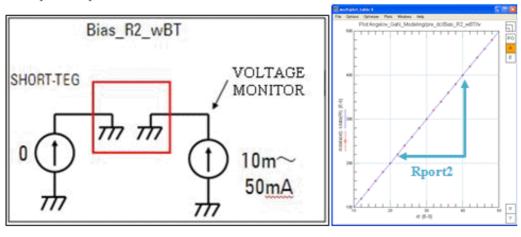
Example of iv plot



PreDC Port2

Calculate Rport2, the DC Path Resistance of Port2 side from the Slope using E:Rport2

Example of iv plot



3. SP Cold FET

SP Cold FET

Here you can calculate the resistence and industnce components by ColdFET method. Since this is the initial value, you need to implement tuning later.

Calculate the resistances RG, RD and RS from R11, R22, R30 using E:RG,RD,RS.
 In the frequency input prompt that appears, enter the flat range in low frequency part of R11, R22 and R30 for resistence component and implement the Extraction.
 If there is no flat range, you may also use the region used for design.
 Extraction results in R11=RG, R22=RD and R30=RS.

Example of prompt (input low frequency) Enter the lower frequency [Hz] to extract the resistances. 5G OK Cancel

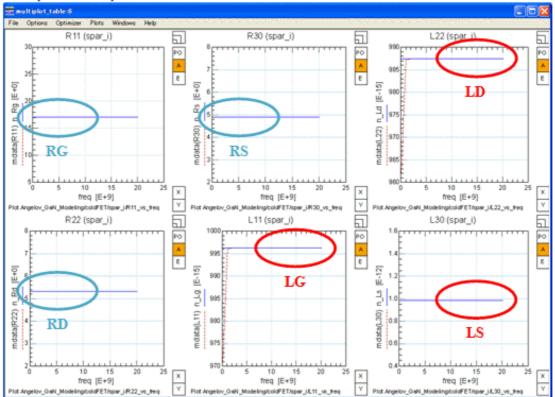
Exa	Example of prompt (input high frequency)									
E	nter	the	higher	freqency	[Hz]	to	extract	the	resistances.	
1	.od									
			OK					Cance		

Calculate the inductances LG, LD, LS from L11, L22, L30 using E:LG,LD,LS.
 In the frequency input prompt that appears, enter the flat range in high frequency part of L11, L22 and L30 for inductance component and implement the Extraction. If there is no flat range, you may also use the region used for design.

 Extraction results in L11 LG L22 LD L30 LS

example of prompt (input low frequency)								
Enter the	lower frequency [Hz] to extract the inductances.						
100								
	ОК	Cancel						
Example of p	prompt (input high	frequency)						
Enter the	higher freqency	[Hz] to extract the inductances.						
20G								
OK Cancel								

Example of Rx/Lx plot



4. Gate Diode

DC gate diode forward

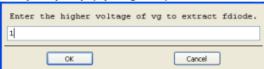
Here you can implement the Extraction and Optimization of forward Gate current.

Calculate IJ, PG, VJG from Ig, using E: IJ,PG,VJG

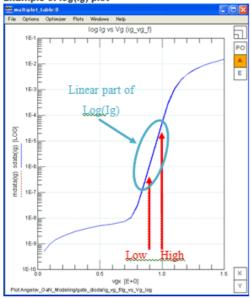
In the bias input prompt that appears, enter the range in linear part of log (Ig) and implement the Extraction of IJ, PG and VJG. Example of prompt (input low bias)



Example of prompt (input high bias)

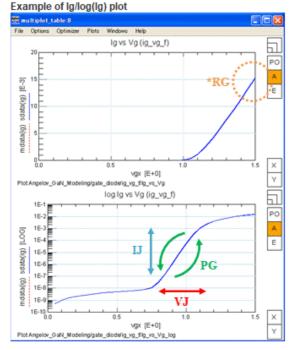


Example of log(lg) plot



Optimization using O: IJ,VJG,T:IJ,VJG
 Keeping the Gate current (Ig, log-Ig) in view, carry out an optimization using IJ and VJG to match the approximate current value.

Optimization using 0: PG
 Keeping the Gate current (Ig, log-Ig) in view, implement an optimization using PG to match the slope of log (Ig).

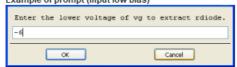


· RG is usually matched with S-parameter.

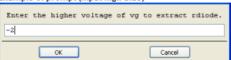
DC gate diode reverse

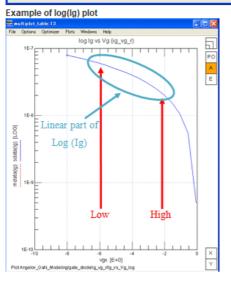
Here you can implement the Extraction and Optimization of reverse Gate current.

Calculate KBGATE, VBDGS, VBDGD and PBGD from Ig using E: KBGATE, VBDGS, VBDGD, PBDG
 In the bias input prompt that appears, enter the range in linear part of log (Ig) and implement the Extraction of KBGATE, VBDGS, VBDGD and PBGD.
 Example of prompt (input low bias)



Example of prompt (input high bias)

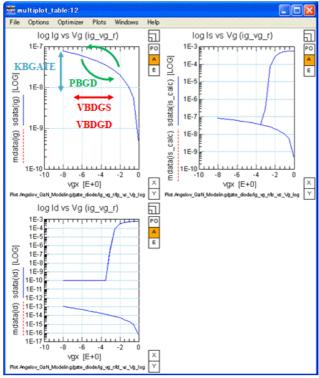




Optimize KBGATE, VBDGS, VBDGD and PBGD using T. KBGATE, VBDGS, VBDGD, PBDG.

Keeping the Gate current (log-Ig) in view, implement an optimization using KBGATE, VBDGS, VBDGD and PBGD to match the approximate current value.

Example of log(lg)/log(ld)/Log(ld) plot



5. idvg & idvd

DC idvg

Here you can implement the Extraction and Optimization of idvg characteristics.

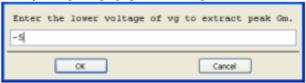
Calculate IPK0, VPKS, P1, P2 and P3 from Id using E: IPK0,VPKS,P1,P2,P3{+}{_}.
 In the bias input prompt that appears, enter the range as shown below:
 Bias before gm is rises up

Bias at which Id starts rising up (Vth vicinity)

Bias which passes over Gm max

And then, implement the Extraction of IPK0, VPKS, P1, P2 and P3.

Example of prompt (input low bias)



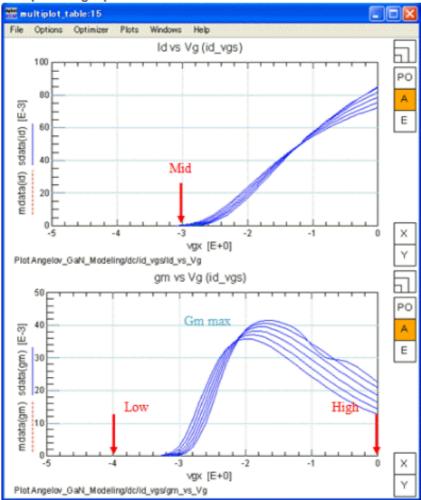
Example of prompt (input mid bias)

Enter	the	mid	voltage	of	vg.
-3					
	OK		Can	cel	

Example of prompt (input high bias)

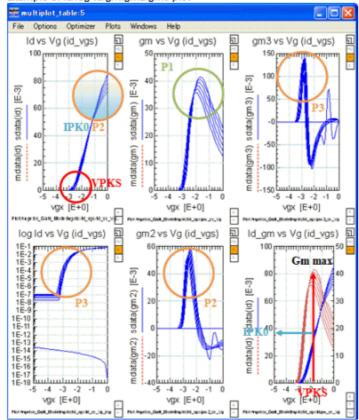
Enter	the	higher	voltage	of	vg	to	extract	peak	Gm.
이									
		OK)				Cancel		

Example of Id/gm plot



- Optimize VPKS, P2 and P3 using O: VPKS,P2,P3{+}{_}.
 Keeping log-ld, gm, gm2 and gm3 in view, match the approximate shape using VPKS, P2 and P3.
- Optimize IPK0, VPKS, P1, P2 and P3 using O: IPK0, VPKS, P1, P2, P3{+}{_}.
 Keeping Id, log-Id, gm, gm2 and gm3 in view, adjust to make the balance (shape) better on the whole, using IPK0, VPKS, P1, P2 and P3.
- Optimize VPKS and P1 using 0: VPKS,P1.
 Keeping log-ld and gm in view, match using VPKS and P1.

Example of Id/log-Id/gm/gm2/gm3 plot



DC idvd

Here you can implement the Extraction and Optimization of idvd characteristics.

1. Calculate LAMBDA from Id using E: LAMBDA.

In the bias input prompt that appears, enter the range as shown below: Bias of linear region

Bias at which the self heating is observed

Bias at which Avalanche current is about to appear or Maximum bias And then, implement the Extraction of LAMBDA.

Example of prompt (input low bias)

Enter	the	lower	voltage of	vd.
2				
	ОК		Cancel	

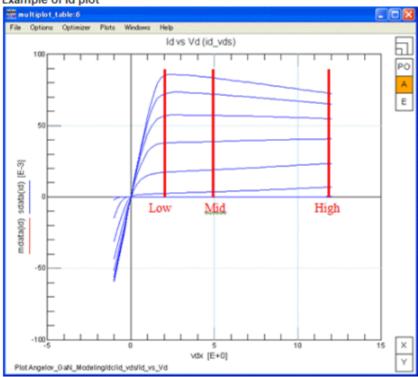
Example of prompt (input mid bias)

Enter	the	mid	voltage	of	vd.
5					
	OK		Can	cel	

Example of prompt (input high bias)

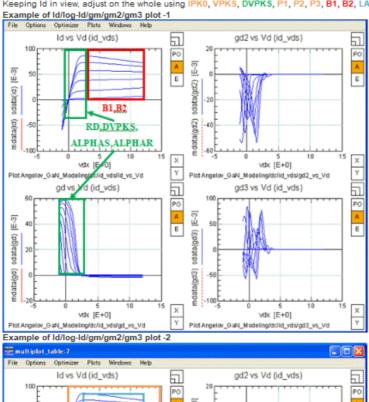
Enter	the	higher	voltage of	vd.
11				
	OK		Cancel	

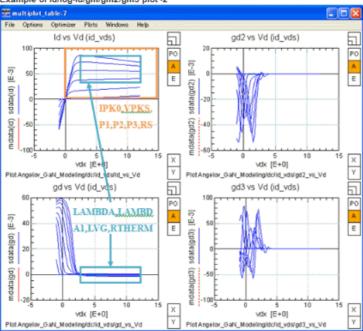
Example of Id plot



- Optimize ALPHAR, ALPHAS and RD using 0: ALPHAR, ALPHAS, RD(+):
 Keeping Id and gds in view, adjust to match with the rising part (linear region) using ALPHAR, ALPHAS and RD.
- Optimize IPK0, VPKS and P1 using 0: IPK0, VPKS, P1(+)(_).
 Keeping Id in view, adjust on the whole using IPK0, VPKS and P1.

- Optimize ALPHAR, ALPHAS and RD using O: ALPHAR, ALPHAS, RD(+)(_).
 Keeping Id and gds in view, adjust to match with the rising part (linear region) using ALPHAR, ALPHAS and RD.
- Optimize IPK0, VPKS, P1, P2, P3, B1, B2, ALPHAR, ALPHAS and RD using O: IPK0, VPKS, P1, P2, P3, B1, B2, ALPHAR, ALPHAS, RD(+)(_).
 Keeping Id and gds in view, adjust on the whole using IPK0, VPKS, P1, P2, P3, B1, B2, ALPHAR, ALPHAS and RD.
- Optimize IPK0, VPKS, DVPKS, P1, P2, P3, B1, B2, LAMBDA, LAMBDA1, LVG, VKN, RD, RS and RTHERM using O: idvd_all(+)(_).
 Keeping Id in view, adjust on the whole using IPK0, VPKS, DVPKS, P1, P2, P3, B1, B2, LAMBDA, LAMBDA1, LVG, VKN, RD, RS and RTHERM.





DC idvg

Once the Extraction and Optimization of idvg and idvd are over, the next step is to implement detailed tuning, keeping both the characteristics in view alternately. Here, you will implement Re-optimization of idvg characteristics.

- Optimize VPKS and P1 using 0: VPKS,P1{+}[_].
 Keeping Id in view, adjust the characteristics using VPKS and P1
- Neeping Ion in Verw, adjust use for alrades issues using VFKS and P1.

 (-) Optimize IPK0, VPKS, P1, P2 and P3 using 0. IPK0,VPKS,P1,P2,P3(-).

 Neeping Id, log-ld, gm, gm2 and gm3in view, adjust on the whole using IPK0, VPKS, P1, P2 and P3.

 Optimize VPKS, P2 and P3 using 0. VPKS,P2,P3

 Neeping Log-ld and gm in view, adjust using VPKS, P2 and P3.

 Tuning IPK0, VPKS, P1, P2 and P3 using 0. IPK0,VPKS,P1,P2,P3(-).

 Neeping Id, log-ld, gm, gm2 and gm3 in view, adjust on the whole using IPK0, VPKS, P1, P2 and P3.

DC idvd

Once the Extraction and Optimization of idvg and idvd are over, the next step is to implement detailed tuning, keeping both the characteristics in view alternately. Here, you will implement Re-optimization of idvd characteristics.

- Optimize ALPHAR, ALPHAS and RD using 0: ALPHAR ALPHAS,RD(+)(_).
 Keeping Id and gds in view, adjust to match with the rising part (linear region) using ALPHAR, ALPHAS and RD.
- Optimize IPK0, VPKS, P1, P2 and RTHERM using O: IPK0, VPKS, P1, P2, RTHERM(+){_}. Keeping Id in view, adjust on the whole using IPK0, VPKS, P1, P2 and RTHERM.

DC idvg

Finally, implement the detailed tuning as the last step of DC modeling. Here, you will implement Re-optimization of idvg characteristics.

Optimize IPK0, VPKS, P1, P2 and P3 using O: IPK0,VPKS,P1,P2,P3{*}{.}
Keeping Id, log-ld, gm, gm2 and gm3 in view, adjust on the whole using IPK0, VPKS, P1, P2 and P3.
This completes the DC part of the modeling, if all the DC characteristics are good with accuracy, you can proceed next for the RF part of the modeling.

6. SP

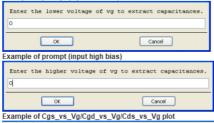
SP vg at vd0 A1

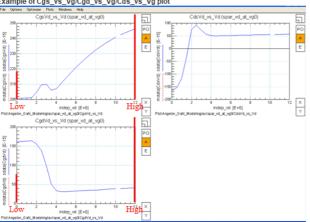
Here, you implement the Extraction of capacitance characteristics when Vd=0. (Implement initial Extraction at Vd=0, Vg=0, and optimization.)

- 1. Calculate CGSPI, CGDPI, CDS, CGS0, CGD0, P10, P11, P40 and P41 from Cgs_vs_Vg, Cgd_vs_Vg and Cds_vs_Vg using E: CGSPI, CGDPI, CDS, CGS0, CGD0, P10, P11, P40, P41{+}. In the bias input prompt that appears, enter the range as shown below: Bias at which the lower capacitance is calculated Bias at which the higher capacitance is calculated

And then, implement the Extraction of CGSPI, CGDPI, CDS, CGS0, CGD0, P10, P11, P40 and P41.

If you enter 0 for all, the whole range is specified.
 Example of prompt (input low bias)





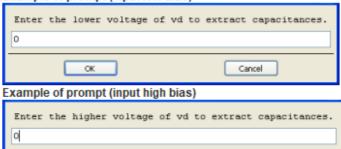
SP vd at vg0

Here, you implement the Extraction of capacitance characteristics when Vg=0. (Implement initial Extraction at Vd=0, Vg=0, and optimize.)

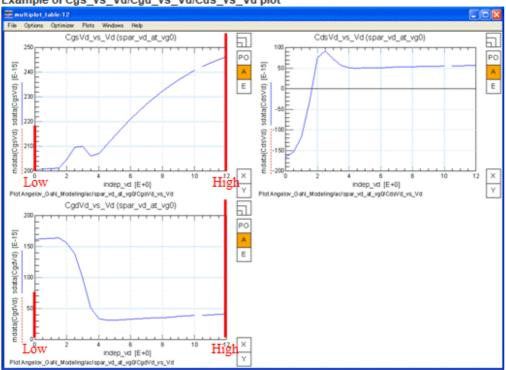
- Calculate P20, P21, P30 and P31 from Cgs_vs_Vd, Cgd_vs_Vd and Cds_vs_Vd using E: P20,P21,P30,P31
 In the bias input prompt that appears, enter the range as shown below:
 Bias at which the lower capacitance is calculated
 Bias at which the higher capacitance is calculated
 And then, implement the Extraction of P20, P21, P30 and P31.
- If you enter 0 for all, the whole range is specified.



OK



Example of Cgs_vs_Vd/Cgd_vs_Vd/Cds_vs_Vd plot



Cancel

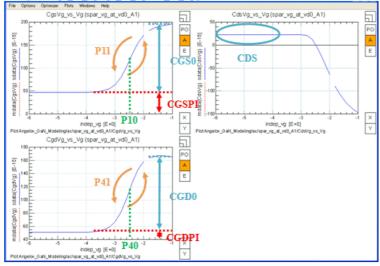
SP vg at vd0 A1

Once the initial Extraction of Cgs, Cgd and Cds are over, the next steps are the optimization of capacitance characteristics and S-Parameter in order. Here, first adjust the capacitance characteristics when Vd=0.

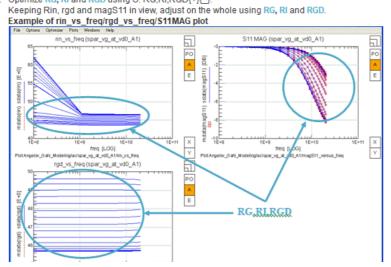
1. Optimize CGSPI, CGDPI, CGS0, CGD0, CDS, P10, P11, P40 and P41 using O: CGS, CGD(+){_}. Adjust the characteristics using

CGSPI, CGS0, P10 and P11, keeping Cgs in view CGDPI, CGD0, P40 and P41, keeping Cgd in view CDS, keeping Cds in view

Example of Cgs_vs_Vg/Cgd_vs_Vg/Cds_vs_Vg plot



2. Optimize RG, RI and RGD using O: RG,RI,RGD(+){_}.



SP vd at vg0

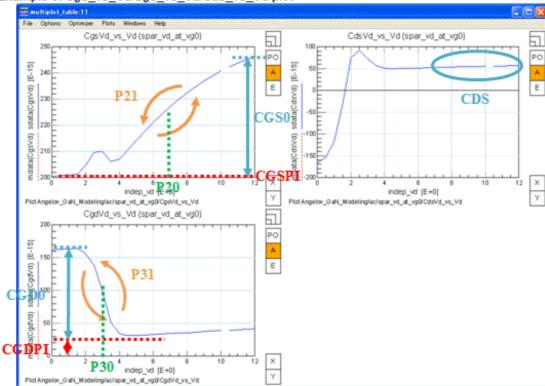
Next go on implementing the optimization of capacitance characteristics and S-Parameter at Vg=0.

 Optimize CGSPI, CGDPI, CGS0, CGD0, CDS, P20, P21, P30 and P31 using O: CGS,CGD Adjust the characteristics using

CGSPI, CGS0, P20 and P21, keeping Cgs in view CGDPI, CGD0, P30 and P31, keeping Cgd in view

CDS, keeping Cds in view

Example of Cgs_vs_Vd/Cgd_vs_Vd/Cds_vs_Vd plot



SP vd at vgm2

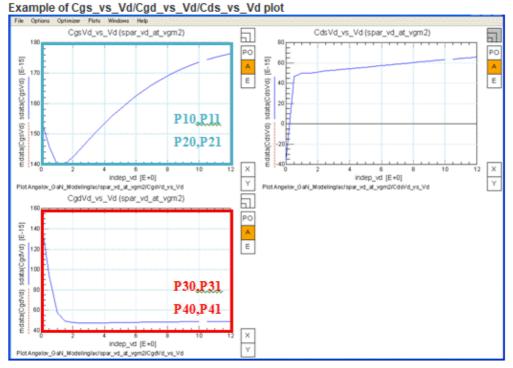
Finally, go on implementing the optimization of capacitance characteristics and S-Parameter with Target bias.

Optimize P10, P11, P20, P21, P30, P31, P40 and P41 using T: CGS,CGD(+){__}.

Adjust the characteristics using

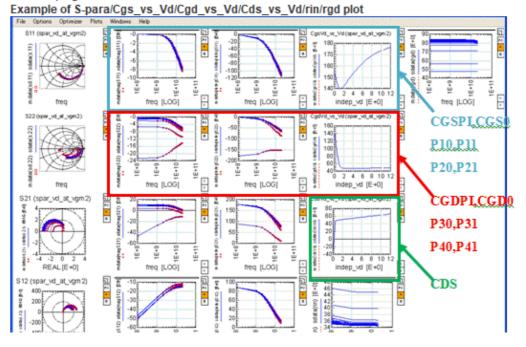
P10, P11, P20 and P21, keeping Cgs in view

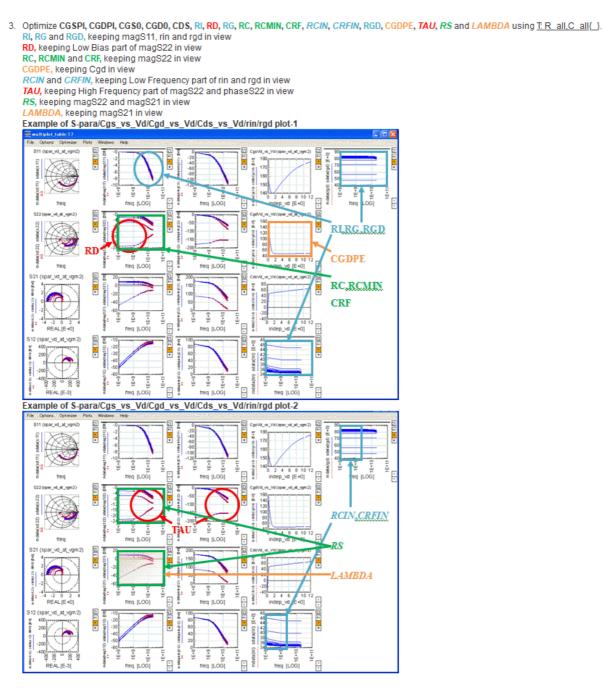
P30, P31, P40 and P41, keeping Cgd in view



Optimize CGSPI, CGDPI, CGS0, CGD0, CDS, P10, P11, P20, P21, P30, P31, P40 and P41 using T: C_all{+}__.
 Adjust the characteristics using

CGSPI, CGS0, P10, P11, P20 and P21, keeping magS11, phaseS11 and Cgs in view CGDPI, CGD0, P30, P31, P40 and P41, keeping magS22, phaseS22 and Cgd in view CDS keeping in view Cds





7. Finalize: Saving all parameters in the model files

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